

## Série N3: « Current Sources »

**Données de la technologie:**  $V_{DD} = 1.8 \text{ V}$ ,  $L_{\min} = 0.18 \mu\text{m}$ ;  $C_{ox} = 8\text{fF}/\mu\text{m}^2$

**nMOS:**  $k_{p,n} = 184 \mu\text{A}/\text{V}^2$ ;  $V_{Tn} = 0.3 \text{ V}$ ;  $U_{a,N} = 4.6 \text{ V}/\mu\text{m}$ ,  $n=1.2$     **pMOS:**  $k_{p,p} = 43 \mu\text{A}/\text{V}^2$ ;  $V_{Tp} = 0.45 \text{ V}$ ;  $U_{a,P} = 12.5 \text{ V}/\mu\text{m}$ ;  $n=1.3$

### Exercise N1 : Self Biasing wide swing current mirror

1. Determine R for a maximum output dynamic range.

The maximum output swing is achieved for a  $V_{D,2} = V_{D,sat} = V_G - V_{Tn}$

$M_4$  and  $M_2$  having the size and drain current  $\rightarrow V_{GS4} = V_G$

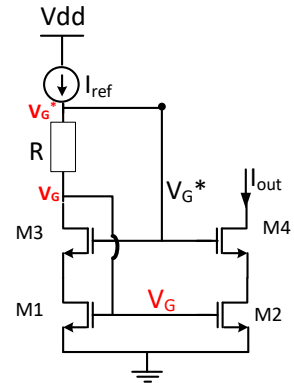
$\rightarrow V_G^* = V_{GS4} + V_{D2} = 2V_G - V_{Tn}$ . Since  $V_G^* - V_G = R I_{ref}$

$\rightarrow R = (V_G - V_{Tn})/I_{ref}$

2. Determine the maximum values of  $R \cdot I_{ref}$  such that  $M_3$  remains in saturation.

$M_3$  in saturation  $\rightarrow V_{D3} > V_{G3} - V_{Tn}$ , since  $V_{D3} = V_G$  and  $V_{G3} = V_G^*$

$\rightarrow V_G^* - V_G < V_{Tn} \rightarrow R I_{ref} < V_{Tn}$



### Exercise N2 : Wide swing current mirror

$(W/L)_{1,2,6,5} = 20/1$ ,  $(W/L)_{3,4} = 60/1$ ,  $I_{ref} = I_1 = 100 \mu\text{A}$

1. Determine  $V_G$ ,  $V_G^*$  and R for a maximum output dynamic range.

$V_G = ?$

Inversion factor of M1:

$$I_{F1} = \frac{I_{D1}}{I_{S1}} = \frac{I_{ref}}{2nk_{p,n} \frac{W}{L} U_T^2} = \frac{100}{2 \cdot 1.2 \cdot 184 \cdot 20 \cdot 0.026^2} \approx 16 > 10$$

$\rightarrow M1$  in strong inversion

$V_{G1}$  can be calculated using the square law as

$$V_G = \sqrt{\frac{2I_{ref}}{k_{p,n}(\frac{W}{L})}} + V_{To,n} = \sqrt{\frac{2 \cdot 100}{184 \cdot 20}} + 0.3 \quad V_G = 0.53 \text{ V}$$

$V_G^* = ?$

The maximum output swing is achieved for a  $V_{D,3} = V_{D,sat} = V_G - V_{Tn} \rightarrow V_G^* = 2V_G - V_{Tn} = 0.76 \text{ V}$

$R = ?$

$$R I_{ref} = V_{G6} - V_G^* = V_{GS6} + V_{G5} - V_G^*$$

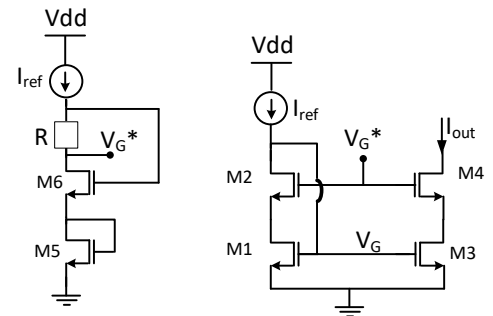
$M_{1,2,6,5}$  with the same sizes and same drain current results in  $V_{GS6} = V_{G5} = V_G = 0.53 \text{ V}$

$\rightarrow R I_{ref} = 2V_G - V_G^* = V_{Tn}$  and  $R = V_{Tn}/I_{ref} = 0.3/100\mu = 3 \text{ k}\Omega$ .

2. Estimate the deviation of  $I_{out}$  from  $300 \mu\text{A}$  if the drain voltage of  $M_4$  is higher than  $V_G$  by  $1 \text{ V}$ .

$\Delta I_{out} = ?$  for a  $\Delta V_{out} = 1 \text{ V}$

$$\Delta I_{out} = r_{o,casc}^{-1} \Delta V_{out} \approx (g_{m4} r_{o4}^2)^{-1} \Delta V_{out}$$

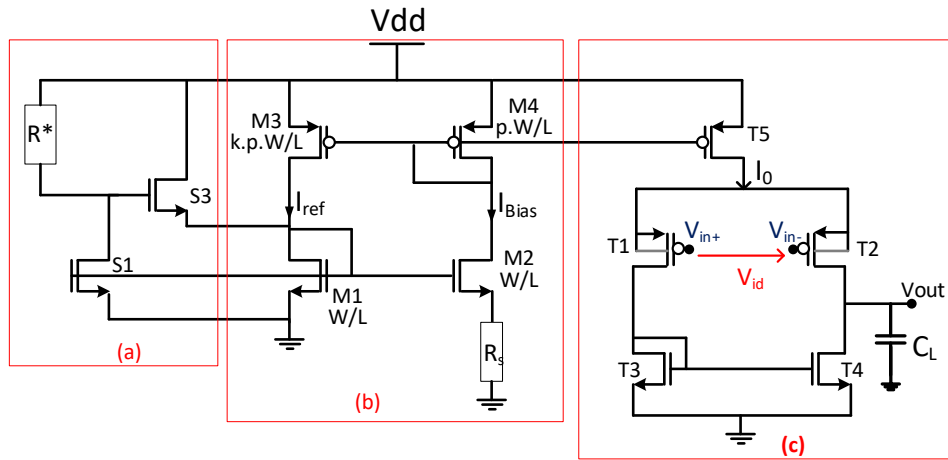


$$\text{With } g_{m4} = \sqrt{2k_{p,n}(W/L)I_{out}} = \sqrt{2 \cdot 184 \cdot 60 \cdot 300} = 2573 \mu S$$

$$r_{o4} = \frac{L \cdot U_a}{I_{out}} = \frac{4.6}{300 \cdot 10^{-6}} = 15.333 \text{ k}\Omega$$

$$\rightarrow \Delta I_{out} = (2573 \cdot 15.33)^{-1} = 1.53 \mu A$$

### Exercise N3 : Biasing circuit for OTA



#### 1. Explain the operation of (a).

The circuit (a) is a start-up circuit that will enable to avoid the degenerated state  $I_{ref} = 0$  of the  $\beta$ -multiplier (b). In fact, when  $I_{ref}$  is null,  $V_{GS,S3}$  equals  $V_{dd}$  and a significant current is injected by S3 into the drain of M1. This will trigger the positive feedback and set  $I_{bias}$  to its desired study-state value defined by  $R_s$ . At the same time  $V_{GS,S3}$  decreases and should go below  $V_{T0}$  at the study state to cancel the impact of the start-up circuit on the  $\beta$ -multiplier operation.

#### 2. Explain the operation of (b) and size all its transistors and $R_s$ to meet the following specifications: $I_{BIAS} = 10 \mu A$ , $V_{ov,n1} = V_{ov,p} = 0.2 \text{ V}$ and $k=4$ .

The circuit (b) is a Beta-multiplier (see the course for the operation).

$$\text{We can demonstrate that } I_{Bias} = \frac{2}{\beta_1 R_s^2} (\sqrt{k} - 1)^2$$

If we know  $v_{ov}$  of M1 we can calculate its  $W/L$

$$M1 \rightarrow \left(\frac{w}{L}\right)_1 = \frac{2kI_{bias}}{k_{p,n}V_{ov}^2} \text{ and for } M3 \rightarrow \left(\frac{w}{L}\right)_3 = \frac{2kI_{bias}}{k_{p,p}V_{ov}^2}$$

NA:

$$(W/L)_{1,2} = 11; (W/L)_3 = 46; (W/L)_4 = (W/L)_3 = 11.5$$

$$R_s \approx 10 \text{ k}\Omega$$

Note:  $V_{ov2} = V_{ov1} - R_s I_{Bias} = 0.1 \text{ V} (< 0.2 \text{ V}) \rightarrow$  Moderate inversion this can result in some inaccuracy that should be evaluated by simulation and eventually corrected by decreasing the sizes  $(W/L)_{1,2}$ .

We can also start by  $V_{ov2} = 0.2 \text{ V}$  to be sure that M2 is in strong inversion  $\rightarrow (W/L)_{1,2} = 2.7 \rightarrow R_s \approx 20 \text{ k}\Omega$  ( $V_{ov1} = V_{ov2} + R_s I_{Bias} \approx 0.4 \text{ V}$ )

#### 3. If the all nMOS transistors of (a) and (b) have the same size, propose a value for $R^*$ .

At study-state the transistor S3 should be switched off in order to don't disturb the Beta-multiplier. For the following condition have to be fulfilled:

$$V_{G,S3} - V_{G,M1} < V_{T0n} \rightarrow V_{dd} - R^* I_{ref} - V_{G,M1} < V_{T0n} \rightarrow R^* > (V_{dd} - V_{ov1} - 2V_{T0n}) / I_{ref}$$

$$R^* > 25 \text{ k}\Omega \text{ } (> 20 \text{ k}\Omega \text{ if we chose } V_{ov1} = 0.4 \text{ V}).$$